



Monocrystalline Wafer

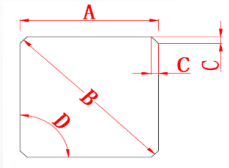
Comprehensive system certification

ISO 9001:2015

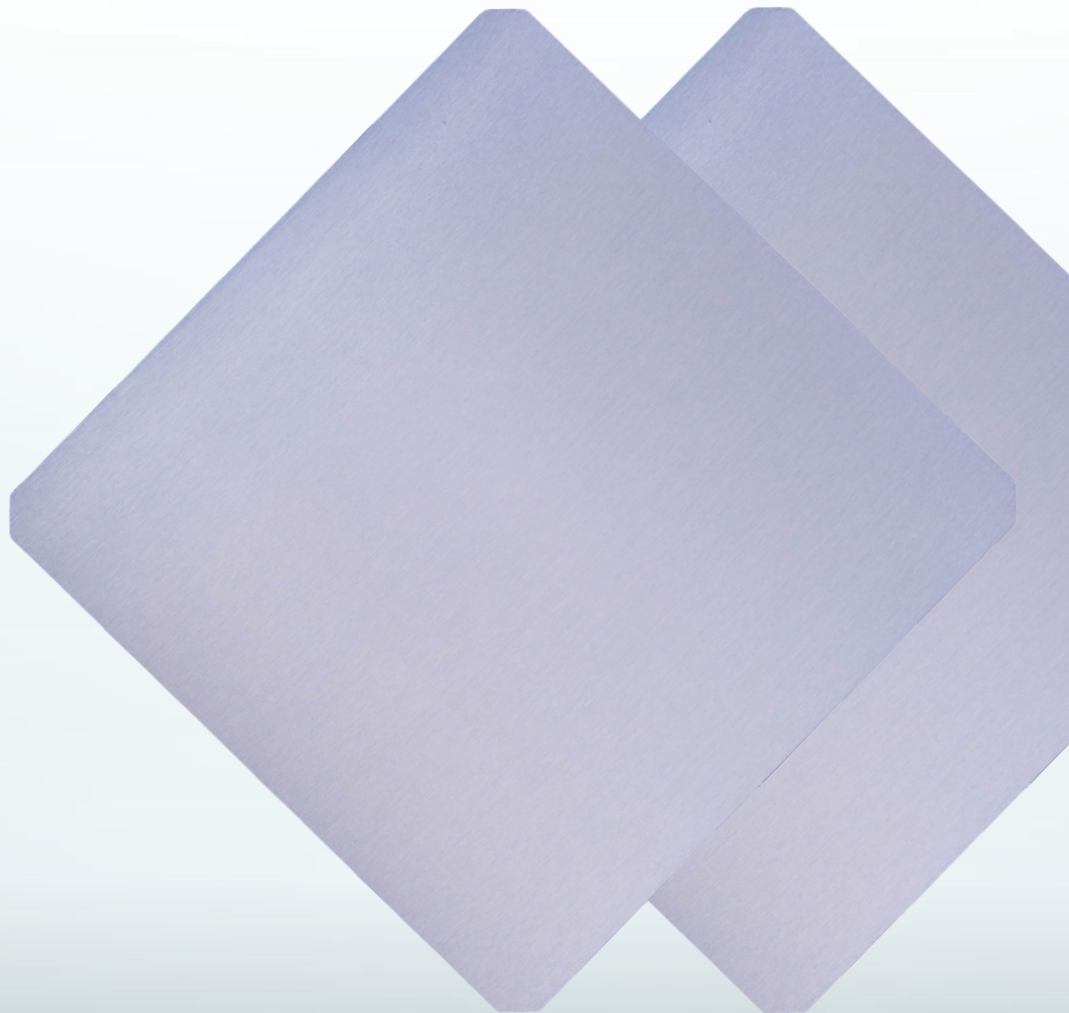
ISO 14001:2015

OHSAS 18001:2018

Schematic diagram of wafer size



Size: M10
A: 182.2 ± 0.25 mm
B: $\phi 247 \pm 0.25$ mm
C: 7.72 ± 0.5 mm
D: $90 \pm 0.15^\circ$



P-type-M10-Res0.4~1.1-A Grade

Monocrystalline Wafer Specification

P-type-M10-Res0.4~1.1-A Grade

Key parameters

| | | |
|--|---------------------------|--|
| Conductivity type | P-type | P/N type tester(DLY-2 P/N) |
| Dopant | Ga. (稼) | -- |
| Resistivity/ Ω .cm | 0.4-1.1 | Wafer inspection system |
| MCLT(Minority carrier lifetime)/ μ s | ≥ 70 | QSSPC /Transient with injection level:1E15cm ⁻³ (Sinton BCT-400) |
| Oxygen concentration [Oi]/at/cm ³ | $\leq 7.5 \times 10^{17}$ | FTIR(ASTM F121-83) |
| Carbon Concentration [Cs]/at/cm ³ | $\leq 5.0 \times 10^{16}$ | FTIR(GB/T 1558-2009) |

Material properties

| | | |
|--|--|---|
| Growth method | CZ | -- |
| Crystallinity | Monocrystalline | -- |
| Etch pit density (dislocation density)/pcs/cm ² | ≤ 500 | Preferential Etch Techniques(ASTM F47-88) |
| Surface orientation/ $^{\circ}$ | $\langle 100 \rangle \pm 3$ | X-ray Diffraction Method (ASTM F26-1987) |
| Orientation of pseudo square sides/ $^{\circ}$ | $\langle 010 \rangle, \langle 001 \rangle \pm 3$ | X-ray Diffraction Method (ASTM F26-1987) |

Geometric dimensions and surface properties

| | | | |
|--|--|-------------------------|---------------------------------------|
| Wafer model | M10 | -- | |
| Geometry | Pseudo square | -- | |
| Bevel edge shape | Round | -- | |
| Wafer Side length/mm | 182.2 \pm 0.25 | Wafer inspection system | |
| Wafer Diameter/mm | $\phi 247 \pm 0.25$ | Wafer inspection system | |
| Arc length projection/mm | 7.72 \pm 0.5 | Wafer inspection system | |
| Angle between adjacent sides/ $^{\circ}$ | 90 \pm 0.15 | Wafer inspection system | |
| Thickness/ μ m | 155 \pm 10 | 150 \pm 10 | Wafer inspection system |
| Batch mean/ μ m | ≥ 155 | ≥ 150 | Wafer inspection system |
| Total thickness variation/ μ m | ≤ 25 | | Wafer inspection system |
| Saw marks/ μ m | ≤ 13 | | Wafer inspection system |
| Bow/ μ m | ≤ 40 | | Wafer inspection system |
| Warp/ μ m | ≤ 40 | | Wafer inspection system |
| Cutting method | DW | -- | |
| Surface quality | as cut and cleaned, no visible contamination,color difference (as determined by standard sample) (oil or grease,finger prints, spot stains, epoxy/glue residue are not allowed) | | Wafer inspection system |
| Chip | depth \leq 0.3mm & length \leq 0.5mm,Max 1/pcs, no V-chip | | Naked eyes or wafer inspection system |
| Micro cracks / holes | Not allowed | | Wafer inspection system |

